Abstracts

Foreword (Mar. 1984 [T-MTT])

H.Q. Tserng and C.C. Huang. "Foreword (Mar. 1984 [T-MTT])." 1984 Transactions on Microwave Theory and Techniques 32.3 (Mar. 1984 [T-MTT] (Special Issue on Power and Low-Noise GaAs FET Circuits and Applications)): 225-225.

Considerable progress has been made over the past several years in power and low-noise GaAs FET's and circuits. Power FET's with output powers of up to 30 W at S-C bands and a few hundred milliwatts at K-band have been achieved. Ultra-low-noise FET's operating at 20 GHz and beyond have been reported. Increasing interest in GaAs monolithic IC technology has also stimulated the steady improvements in discrete power and low-noise FET performance. Special circuit techniques such as large-signal characterization, modeling, and power combining have become increasingly important for realizing the ultimate performance potentials of this important and versatile solid-state microwave device.

❑ Return to main document.